



TIP142T TIP147T

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP - NPN DEVICES
- MONOLITHIC DARLINGTON CONFIGURATION
- LOW VOLTAGE
- HIGH CURRENT
- HIGH GAIN

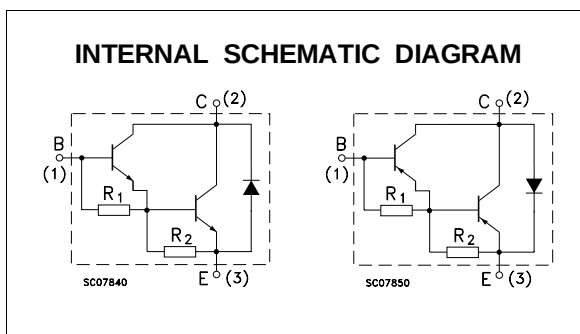
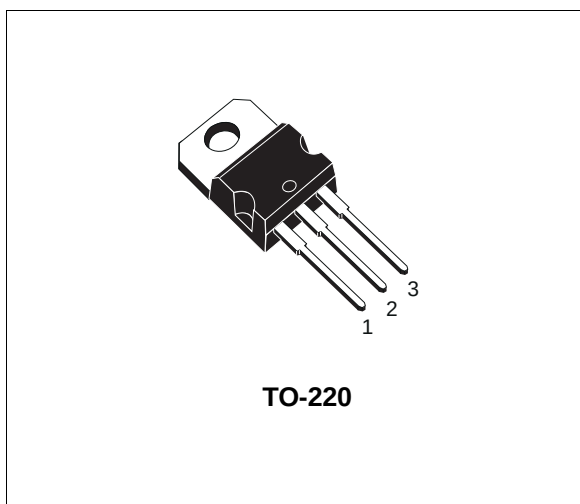
APPLICATIONS

- GENERAL PURPOSE SWITCHING

DESCRIPTION

The TIP142T is a silicon Epitaxial-Base NPN power transistor in monolithic Darlington configuration, mounted in TO-220 plastic package. It is intended for use in power linear and switching applications.

The complementary PNP type is TIP147T.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	NPN	Value	Unit
		PNP	TIP147T	
V_{CBO}	Collector-Base Voltage ($I_E = 0$)		100	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)		100	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)		5	V
I_C	Collector Current		15	A
I_{CM}	Collector Peak Current ($t_p < 5ms$)		20	A
I_B	Base Current		0.5	A
P_{tot}	Total Dissipation at $T_{case} \leq 25^\circ C$		90	W
T_{stg}	Storage Temperature		- 65 to 150	$^\circ C$
T_j	Max. Operating Junction Temperature		150	$^\circ C$

For PNP types voltage and current values are negative.

TIP142T / TIP147T

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	1.38	$^{\circ}C/W$
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

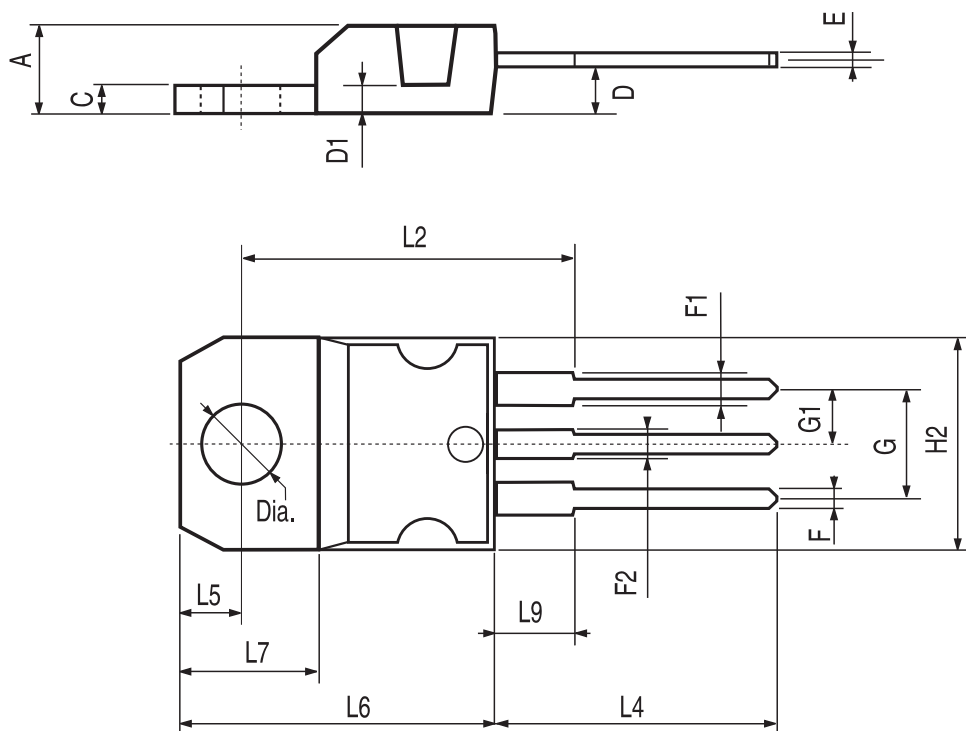
Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = 100\text{ V}$				1	mA
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{CE} = 50\text{ V}$				2	mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5\text{ V}$				2	mA
$V_{CEO(sus)}^*$	Collector-Emitter Sustaining Voltage ($I_B = 0$)	$I_C = 30\text{ mA}$		100			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 5\text{ A}$	$I_B = 10\text{ mA}$			2	V
		$I_C = 10\text{ A}$	$I_B = 40\text{ mA}$			3	V
$V_{BE(on)}^*$	Base-Emitter Voltage	$I_C = 10\text{ A}$	$V_{CE} = 4\text{ V}$			3	V
h_{FE}^*	DC Current Gain	$I_C = 5\text{ A}$	$V_{CE} = 4\text{ V}$	1000			
		$I_C = 10\text{ A}$	$V_{CE} = 4\text{ V}$	500			
t_{on}	RESISTIVE LOAD Turn-on Time	$I_C = 10\text{ A}$	$I_{B1} = 10\text{ mA}$		0.9		μs
t_{off}	Turn-off Time	$I_{B2} = -40\text{ mA}$	$R_L = 3\ \Omega$		4		μs

For PNP types voltage and current values are negative.

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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